

C. Claims

The following is a complete listing of the claims, and replaces all earlier versions and listings.

1. (Previously Presented) A processing apparatus that provides a plasma treatment to an object, said processing apparatus comprising:
 - a process chamber that accommodates an object to be processed and generates plasma;
 - a gas introducing part for introducing gas into the process chamber;
 - a mechanism that arranges the object in a flow of the gas such that the object is between the gas introducing part and a plasma generating region in the flow of the gas; and
 - an exhaust mechanism for exhausting the gas,

wherein the plasma is a microwave excitation surface wave plasma or a microwave excitation surface wave interference plasma.
2. (Original) A processing apparatus according to claim 1, further comprising, between the object and the plasma generating region, a conductance adjuster for maintaining, within a predetermined range, a concentration of active species in a process space that encloses the object.
3. (Original) A processing apparatus according to claim 2, wherein said conductance adjuster is a plate bored with plural holes.

4-5. (Cancelled)

6. (Original) A processing apparatus according to claim 1, wherein the plasma treatment is oxidation or nitridation to a surface of the object.

7-20. (Cancelled).